

ON Semiconductor®

FDC654P

Single P-Channel Logic Level PowerTrench^o MOSFET

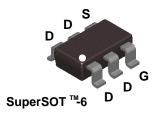
General Description

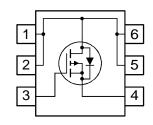
P-Channel Level MOSFET Logic produced using ON Semiconductor's advanced PowerTrench process. It has been optimized for battery power management applications.

Applications

- · Battery management
- · Load switch
- · Battery protection

- $R_{\text{DS(ON)}}$ = 125 $m\Omega$ @ V_{GS} = -4.5~V
- Low gate charge (6.2 nC typical)
- High performance trench technology for extremely low R_{DS(ON)}





Absolute Maximum Ratings T_{A=25°C} unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current - Continuous	(Note 1a)	-3.6	А
	– Pulsed		-10	
P _D	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
T_J, T_{STG}	Operating and Storage Junction Temp	erature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.654	FDC654P	7"	8mm	3000 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1	I	I	I	
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to $25^{\circ}C$		-22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-1	-1.9	-3	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$, Referenced to 25°C		4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -10 \text{ V}, I_D = -3.6 \text{ A}$ $V_{GS} = -4.5 \text{ V}, I_D = -2.7 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -3.6 \text{A}, T_J = 125 ^{\circ}\text{C}$		63 100 90	75 125 115	mΩ
I _{D(on)}	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, \qquad V_{DS} = -5 \text{ V}$	-5			Α
g Fs	Forward Transconductance	$V_{DS} = -5 \text{ V}, \qquad I_{D} = -3.6 \text{ A}$		6		S
Dvnamio	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V},$		298		pF
Coss	Output Capacitance	f = 1.0 MHz		83		pF
C _{rss}	Reverse Transfer Capacitance			39		pF
Switchin	ng Characteristics (Note 2)	1	I	I	I	
d(on)	Turn-On Delay Time	$V_{DD} = -15 \text{ V}, \qquad I_{D} = -1 \text{ A},$		6	12	ns
tr	Turn-On Rise Time	$V_{GS} = -10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		13	23	ns
d(off)	Turn-Off Delay Time			11	20	ns
f	Turn-Off Fall Time			6	12	ns
Q_q	Total Gate Charge	$V_{DS} = -15 \text{ V}, I_{D} = -3.6 \text{ A},$		6.2	9	nC
Q_{gs}	Gate-Source Charge	V _{GS} = -10 V		1		nC
Q_{ad}	Gate-Drain Charge			1.2		nC
Drain_S	ource Diode Characteristics	and Maximum Ratings				
_S	Maximum Continuous Drain–Source				-1.3	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -1.3 \text{ A} \text{(Note 2)}$		-0.8	-1.2	V

Notes:

^{1.} R_{8JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{8JC} is guaranteed by design while R_{8CA} is determined by the user's board design.



a) 78°C/W when mounted on a 1in² pad of 2 oz copper



b) 156°C/W when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%

Typical Characteristics

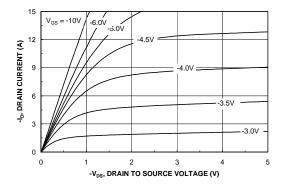


Figure 1. On-Region Characteristics.

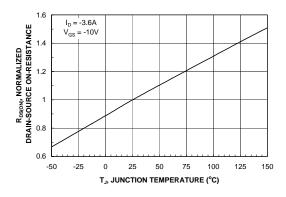


Figure 3. On-Resistance Variation with Temperature.

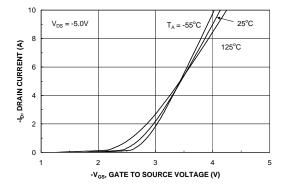


Figure 5. Transfer Characteristics.

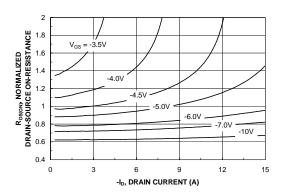


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

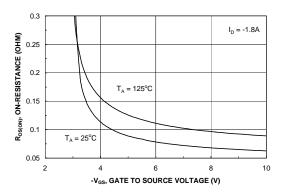


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

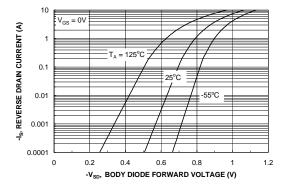
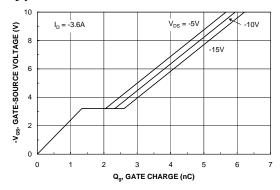


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



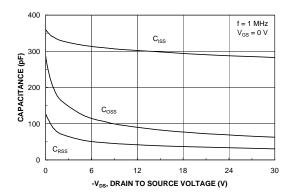
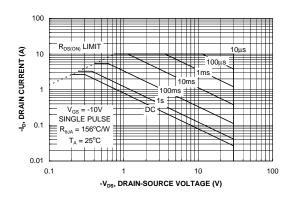


Figure 7. Gate Charge Characteristics.





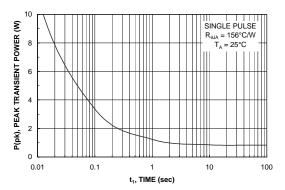


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

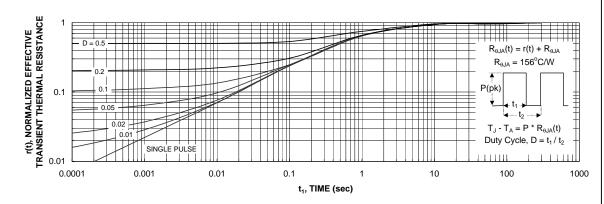


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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